

Impact of environmental stresses on Low Gain Avalanche Diodes

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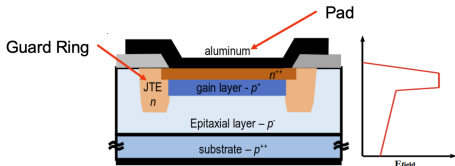
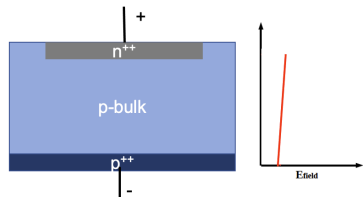
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December 1, 2023

Introduction: Low Gain Avalanche Detectors

LGAD characteristics and its applications

- Good candidate for timing measurements.
- Variety of applications, such as HEP, Nuclear Physics, medical imaging etc.
- Application to space-based experiments starting to be investigated.



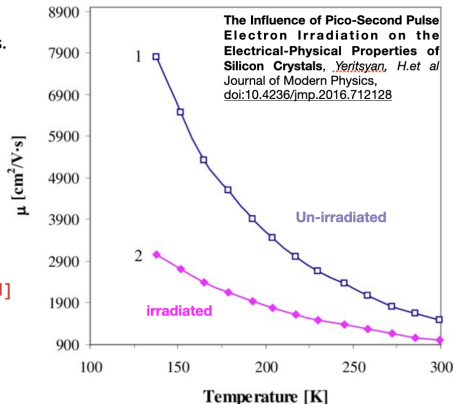
- Standard Silicon Diode
- Gain = 1
- Signal/Noise Ratio is low

- Standard Silicon Diode
- Gain $\sim 10 - 100$
- Signal/Noise Ratio very high
- Timing resolution $\sim 30\text{ps}$

Environmental conditions

- A large set of studies actively performed on LGADs & AC-LGADs
 - In cryogenic and laboratory-controlled conditions.
- Space applications require the study of LGAD behavior in a wide range of environmental conditions.
 - Temperature variations -100°C and $+100^{\circ}\text{C}$
 - Payload limitations: temperature control not ensured
- Charge carrier mobility:
 - Decreases as temperature increases due to phonon scattering.
 - The mobilities decrease as the doping concentration increases due to the scattering from the dopants.

➔ Gain reduction as a function of temperature increase [1]
- Need to ensure good sensor response and electrical characteristics at varying operating conditions.



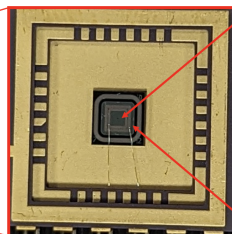
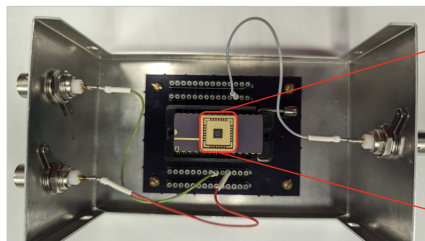
Silicon crystal (n -Si) charge carrier's mobility temperature dependence after electron pico-second beam irradiation (3.5 MeV).

[1] Gain suppression mechanism observed in Low Gain Avalanche Detectors, *Esteban Currás, Marcos Fernández, Michael Moll* [arXiv:2107.10022](https://arxiv.org/abs/2107.10022)

Sensors and Setups

DC-LGAD made at Brookhaven National Laboratory

- 50 μm thickness sensor is mounted to a readout chip.
- Sensor is biased with high voltage.
- Leakage currents from pad and guard ring of the sensor are measured.
- With and without a passivation layer.



Pad

Guard Ring

Sensors and Setups

- Different setups are used in our study.
 - BNL setup.
 - RD50 setup.

	BNL setup	RD50 setups
Probe-station setups used in reverse bias	climate chamber with two-needle probe-station readout (compliance at 10–6 A/V).	characterization laboratory, with a two-needle probe station setup (compliance at 10–6 A/V).
Thermal and humidity control	ambient chamber $T = -60^{\circ}\text{C}$ to $T = +180^{\circ}\text{C}$ with varying humidity. The setup is kept inside an ambient chamber for thermal cycle	ethanol chiller for cooling and heating in the ranges of $T = -30^{\circ}\text{C}$ to $T = +30^{\circ}\text{C}$. dry air for humidity control 20-30%
	N2 is supplied to vary relative humidity and to prevent condensation when operating at cryogenic temperatures	



Humidity and temperature are measured inside the metal box (BNL)



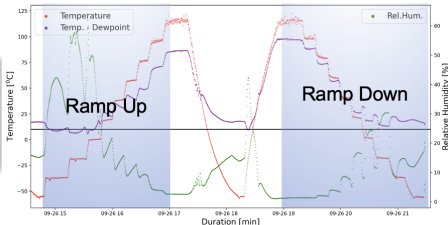
Humidity-controlled environments with dry-air desiccators(CERN)

Thermal cycle

- Temperature of the ambient chamber is cycled at an average rate of 1.81 °C/mn.
- Humidity is maintained in such manner that dew point is always 10 °C less than the operating temperature of the ambient chamber.

Program	Temperature	Bias Voltage	IV Measurements
Day	-60 °C to 120°C	-50 V	Steps of 20°C: Ramping up and ramping down
Night	21 °C	-150 V	No measurement
Weekend	10 °C to 120°C	off	No measurement

- The temperature range is driven by the limitations of ambient chamber and electrical components

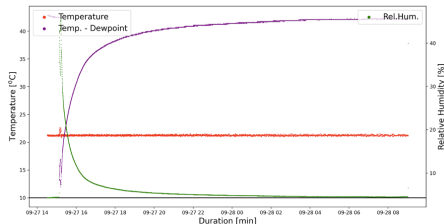


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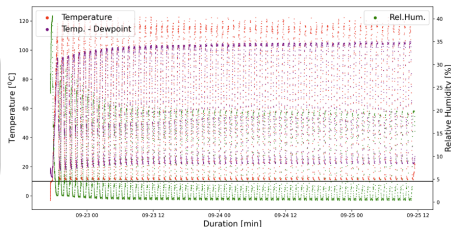


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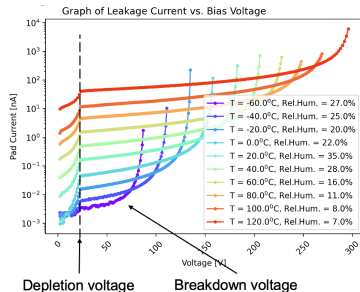
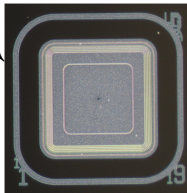
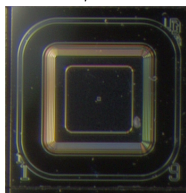
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Use of different wafers: W3045 vs W3058

- Sensors testing from two different wafers fabricated at BNL
- W3045: First production, no passivation, no termination.
- W3058: Latest production, Silicon nitride/oxide passivation, Improved termination and contact

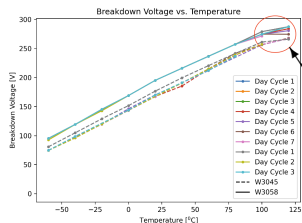


Observation

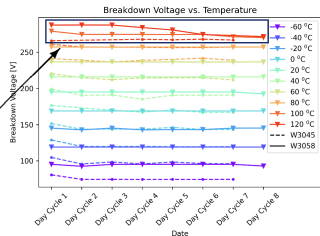
- Depletion voltage is independent of temperature.
- Breakdown voltage increases with temperature
- Leakage current of plateau increases with temperature

Breakdown voltage results

- Breakdown voltage is estimated by two linear fits on the IV curve.



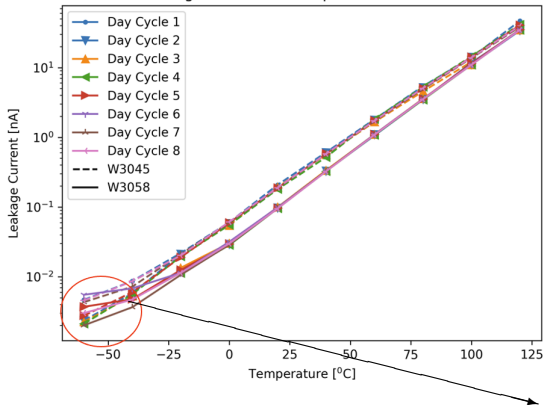
- This discrepancy is a primary result of fitting code artifact



- Breakdown voltage increases linearly with the temperature
- New sensor shows improvement in breakdown voltage compared to the old sensor
- Breakdown voltage is consistent over different thermal cycles in the new wafer.

Results: Leakage Current vs Temperature

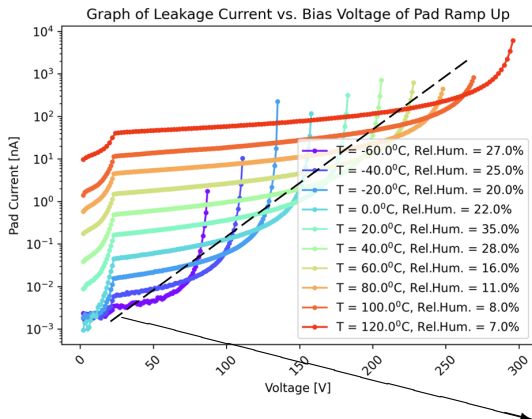
Leakage Current vs. Temperature at -50.0 V



- Leakage current exponentially increases with the temperature.
- Leakage current is consistent over different thermal cycles.
- Leakage current of the new sensors is lower compared to older sensors.

- Current in pA range

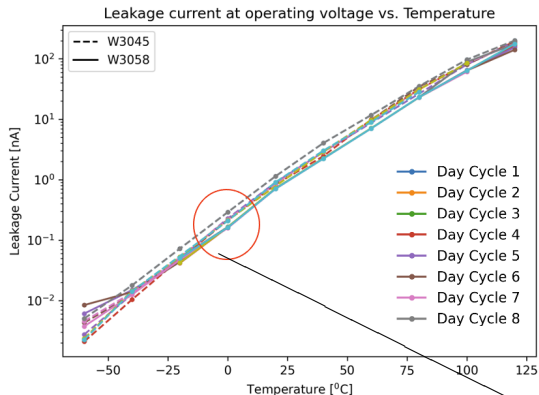
Operating Voltage



- Sensors are operated at the highest voltage before breakdown such that the carrier velocity saturates (in order to improve time response)
- Operating Voltage = Breakdown Voltage – 20 V.

- Operating Voltage

Leakage Current at Operating Voltage

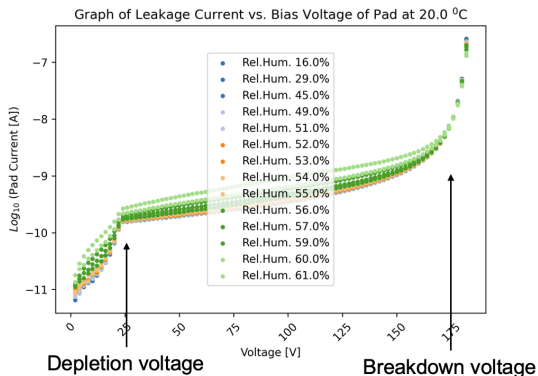


- Leakage current of the new wafer is lower compared to the older wafer at the operating voltage
- New wafer shows consistent leakage current over different thermal cycles showing an excellent improvement from its predecessor
- Dispersion of the leakage current at 0°C over different thermal cycles

- $\sigma_{W3045} = \pm 12.5\%$
- $\sigma_{W3058} = \pm 1.3\%$

Results: Leakage Current and Relative Humidity

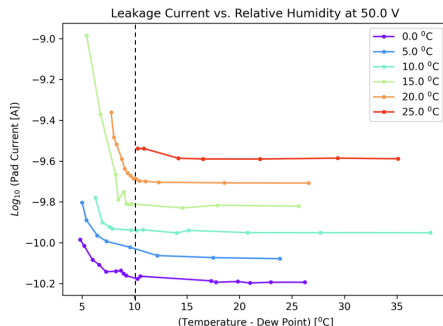
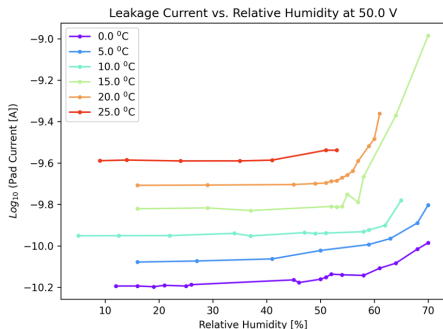
- We keep the temperature constant at 20.0°C and vary the humidity



- Depletion voltage is independent of humidity
- Breakdown voltage is independent of humidity
- Leakage current of plateau increases with humidity

Results: Leakage Current and Dewpoint

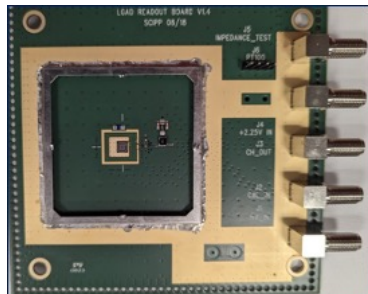
- We repeated the above measurements at different temperatures



- When dewpoint reaches 10°C closer to the temperature, a critical humidity, the leakage current increases rapidly

Experimental Setup: Analog Signal Analysis

- DC-LGAD sensor is mounted to a readout board to measure analog signal pulses
- This setup is kept inside the ambient chamber together with IV setup and thermal cycled simultaneously



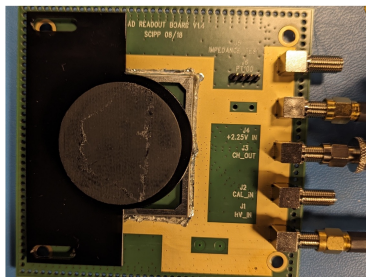
LGAD READOUT BOARD
V1.4 SCIPP 08/18



LGAD Readout board inside the
ambient chamber

Experimental Setup: Analog Signal Analysis

- Analog signal analysis is performed before and after thermal cycling
- We use a Sr90 as signal source and measure the analog pulse using Waverunner 9404M-MS oscilloscope
- Signals are recorded outside the ambient chamber in an uncontrolled environment at room temperature inside a dark hood



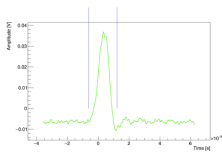
Sr 90 Beta source is used to generate signal pulses



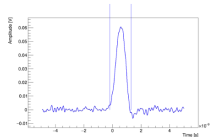
Analog signal pulses recorded by oscilloscope

Signal Pulse Amplitude

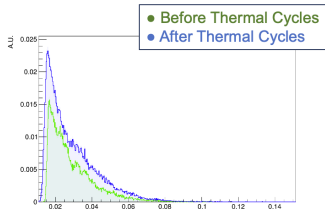
- Sample waveform of a signal measured before and after 8 thermal cycles.



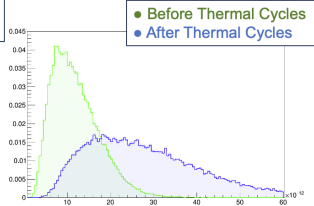
Before Thermal Cycles



After Thermal Cycles



Amplitude [V]



Jitter [s]

Summary of Analog Signal

- Signal amplitude is consistent before and after thermal cycles.
- We observe the noise of the signals to have increased significantly.
- This discrepancy can be attributed to the electronics of readout board being impacted due to thermal cycling.

Thermal Cycles	Amplitude [mV]	Noise [mV]	Slew Rate [MV/s]	Jitter [ps]
Before Thermal Cycles	20.9°C	0.48	36.5	9.68
After 8 Day Cycles + 2 Weekend Prog.	19.1°C	0.99	31.2	26.3

As this is a work in progress, we anticipate to perform a more comprehensive analog signal analysis in the future

Conclusion and Outlook

- Two different BNL-made LGAD sensors have been tested for weeks at extreme and rapidly changing temperature and humidity conditions.
- The results from the two sensors show consistent response of leakage current, and depletion, breakdown and operating voltages as functions of temperature and humidity.
- no deterioration of performance is seen in LGADs after weeks of thermal-cycling
- The new LGADs with an improved termination design shows slightly better performance than the old sensor design

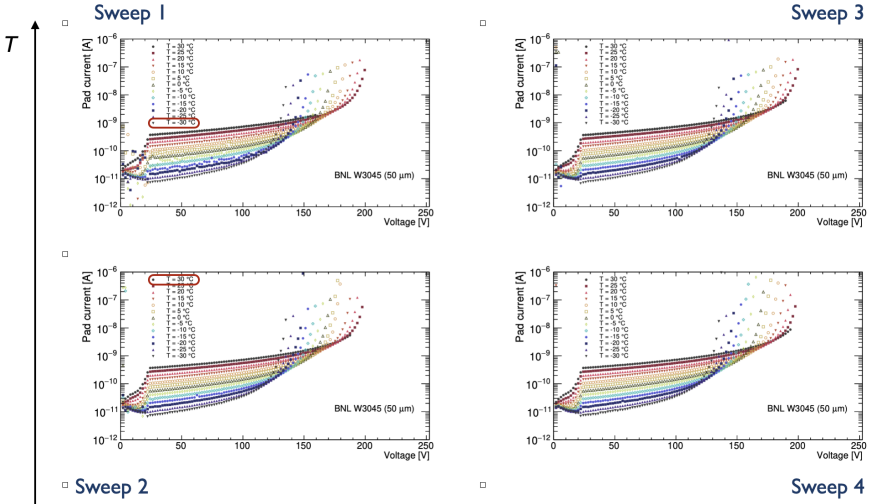
Parameters	Depletion Voltage	Breakdown Voltage	Leakage Current
Temperature	Independent	Dependent	Dependent
Humidity	Independent	Independent	Critical Humidity

- Thermal cycles will continue for several more weeks and performance will be assessed to test the limits of LGADs. Similar tests will be performed in the future for AC-LGADs and for sensors after irradiation.

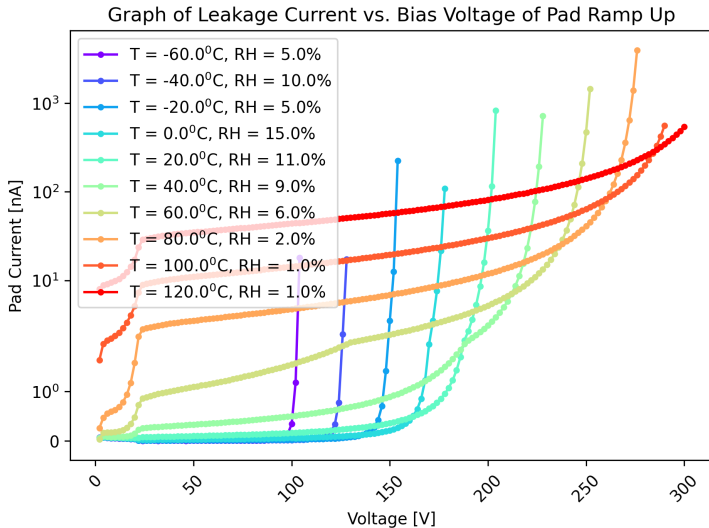
BACKUP

Thermal Profile

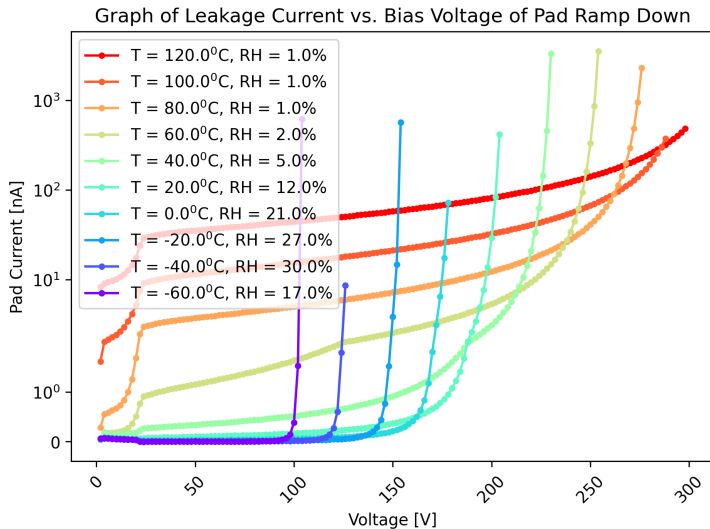
- Studies repeated for stability under rapidly changing conditions.
 - by abruptly changing the temperature changes between the cold (-30°C) and warm regimes (+30°C)



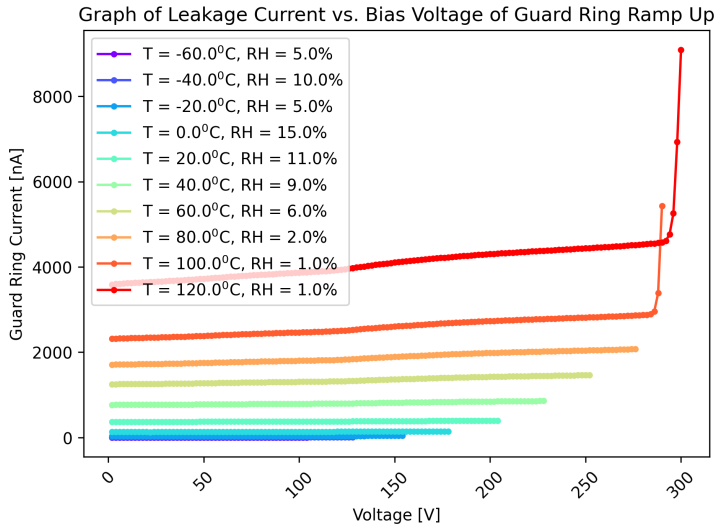
Pad current vs Bias voltage: Ramp up



Pad current vs Bias voltage: Ramp down



Guard Ring current vs Bias voltage: Ramp up



Guard Ring current vs Bias voltage: Ramp down

Graph of Leakage Current vs. Bias Voltage of Guard Ring Ramp Down

